


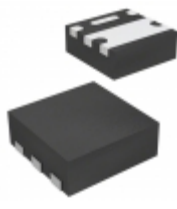




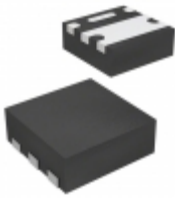
	<h2>SIA447DJ-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA447DJ-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 12V 12A SC-70-6L</p> <p>Datenblätter:  SIA447DJ-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 49601 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA447DJ-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 12V 12A SC-70-6L
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	49601 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.5W (Ta), 19W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	12A (Tc)
Rds On (Max) @ Id, Vgs	13.5 mOhm @ 7A, 4.5V
VGS (th) (Max) @ Id	850mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	80nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	2880pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)




SIA447DJ-T1-GE3 ist neu im Original, Suche SIA447DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA447DJ-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SIA447DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA445EDJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 12A SC-70</p>	 <p>SIA447DJ-T1-E3 VISHAY VISHAY QFN-6</p>	 <p>SIA446DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 150V 7.7A SC70-6L</p>	 <p>SIA447DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 12A SC-70-6L</p>
 <p>SIA446DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 7.7A SC70-6L</p>	 <p>SIA448DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 12A SC70-6L</p>	 <p>SIA449DJ-GE3 Vishay Precision Group SIA449DJ-GE3 VISHAY</p>	 <p>SIA448DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 12A SC70-6L</p>

heiße Teile

Mehr

 SIA426DJ-T1-GE3	 SIA427DJ-T1-GE3	 SIA427DJ-T1-GE3	 SIA429DJ-T1-GE3	 SIA429DJ-T1-GE3
 SIA430DJ-T1-GE3	 SIA430DJ-T1-GE3	 SIA431DJ	 SIA431DJ-T1	 SIA431DJ-T1-GE3
 SIA431DJ-T1-GE3	 SIA432DJ-T1-GE3	 SIA432DJ-T1-GE3	 SIA433EDJ	 SIA433EDJ-T1-GE3
 SIA433EDJ-T1-GE3	 SIA436DJ-T1-GE3	 SIA436DJ-T1-GE3	 SIA443DJ-T1-GE3	 SIA443DJ-T1-GE3
 SIA444DJ-T1-GE3	 SIA444DJ-T1-GE3	 SIA445EDJ-T1-GE3	 SIA445EDJ-T1-GE3	 SIA447DJ-T1-GE3
 SIA448DJ-T1-GE3	 SIA448DJ-T1-GE3	 SIA449DJ-GE3	 SIA450DJ-T1-GE3	 SIA450DJ-T1-GE3
 SIA4528-100K	 SIA4528-330K	 SIA4528-470K	 SIA453EDJ-T1-GE3	 SIA453EDJ-T1-GE3
 SIA456DJ-T1-GE3	 SIA456DJ-T1-GE3	 SIA483DJ-T1-GE3	 SIA483DJ-T1-GE3	 SIA513DJ-T1-E3
 SIA517DJ-T1-GE3	 SIA517DJ-T1-GE3	 SIA517DJ-T4-GE3	 SIA519EDJ-T1-GE3	 SIA519EDJ-T1-GE3
 SIA533EDJ-T1-GE3	 SIA533EDJ-T1-GE3	 SIA778DJ-T1-GE3	 SIA778DJ-T1-GE3	 SIA811ADJ-T1-GE3

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